

# TPD-1C12-013

## InGaAs PIN photodiode chip

### FEATURES:

- Optimized for monitor application.
- Low dark current and low capacitance.



### ELECTRO-OPTICAL CHARACTERISTICS:

PARAMETERS	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Responsivity	R		0.9		A/W	$V_R=5V, \lambda=1300nm$
Dark Current	$I_D$		0.3	5	nA	$V_R=5V$
Breakdown Voltage	$V_{BD}$	20	35		V	$I_R=10\mu A$
Capacitance	C		6	15	pF	$V_R=5V, f=1 MHz$

Fig. 1 Typical Dark Current and Forward Current

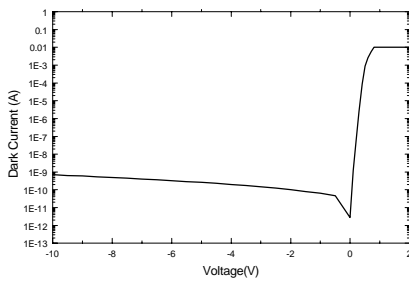


Fig. 2 Typical Photo-Current

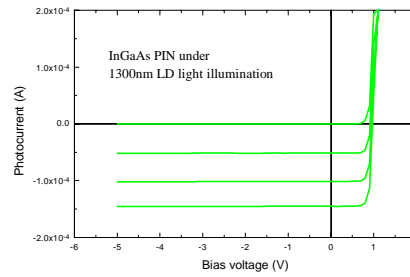


Fig. 3 Typical Breakdown Curve

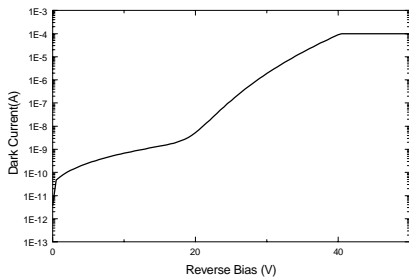
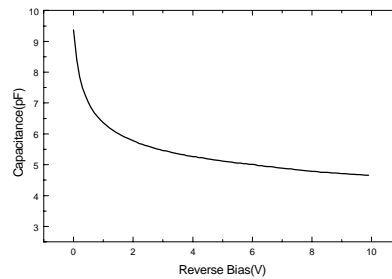
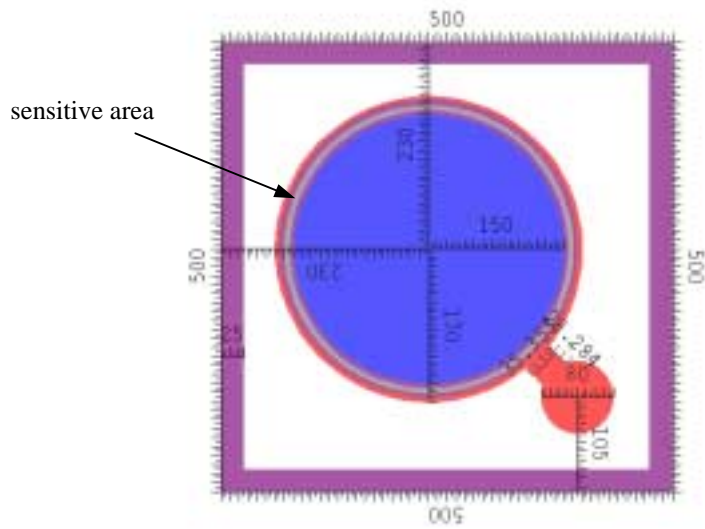


Fig. 4 Typical C-V Curve



## OUTLINE DIAGRAM:



- Chip size is typical 500x500 μm.
- Sensitive area is typical 300 μm in diameter.